

The over current protection of three shunt method

DESCRIPTION

RT8H052C is composed by NPN transistors, PNP transistors and resistors. It can miniaturization of a set and reduce parts or time necessary for completion. This MFT composed the circuit for the over current protection of three shunt method.

FEATURES

- Miniaturization of a set.
- Variable VREF by external resistance.

APPLICATION

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<м г т> RT8H052C

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Symbol	Parameter	Conditions	Ratings	Unit
Vcc	Supply voltage		12	V
VIN	Input voltage		-0.3 ~ Vcc	V
Pd	Internal power dissipation		200	mW
К Ө	Thermal derating	Ta≧25°C	1.6	m₩/°C
Tj	Junction temperature		150	°C
Tstg	Storage temperature	(keep dry)	-40~150	°C
Topr	Operating temperature	Tj (keep dry)	-30~150	°C

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ELECTRICAL CHARACTERISTIC (Ta=25°C, VCC=5V unless otherwise noted.)

Symbol	Parameter	Test conditions	Designed value			llni+
			Min	Тур	Max	
Vcc	Operating supply voltage range		3	5	10	۷
ICC_off	Circuit current of off states	IN1=IN2=IN3=0V、VREF=0.5V		0. 2		mA
ICC_on	Circuit current of on states	IN1=1V、IN2=IN3=0V、VREF=0.5V		2.9		mA
VINCM	Common mode input voltage range		0. 3	-	VCC-0. 8	۷
VIN1th	IN1 threshold voltage	VREF=0.5V、IN2=IN3=0V		0.5		۷
VIN2th	IN2 threshold voltage	VREF=0.5V、IN1=IN3=0V		0.5		V
VIN3th	IN3 threshold voltage	VREF=0.5V、IN1=IN2=0V		0.5		V

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OPERATING EXPLANATION

This MFT have VREF terminal ,so the threshold voltage can be freely set by external connected resistance. MFT doesn't have the output terminal for six pins MFT (VCC, GND, VREF, IN1, IN2, IN3). The terminal VCC uses two functions of the power-supply voltage terminal and the output terminal. The circuit current flows about 200uA, when the threshold voltage does not get over than neither of IN1~IN3 setting of VREF. When the voltage of VREF(V) or more is impressed to either of terminal of IN1~IN3, it enters the state of detection, the circuit current flows to VCC becomes about 2.9mA. By using the characteristic of this circuit current, the output signal can be made by connecting the PNP transistor outside. The output terminal is the collector terminal of the Q1:PNP transistor. At the usual state, the PNP transistor is turning off and output Low. At the detecting state, the PNP transistor is turning on and output High.

SELECTION OF PARTS

How to select the resistance at above application circuit example.

Resistance R1 connected between emitter bases of the Q1:PNP transistor is set to turn on the PNP transistor when the PNP transistor is usually turned off in the circuit current in the state, and the detected circuit current flows about MFT. please set resistance R1 at rage $390 \Omega \sim 1.5 k \Omega$. The current thrown into the Q1:PNP transistor is adjusted by resistance R2 between collectors GND.

Calculation formula, if making VREF from resistance. VREF (V) =R4/(R3+R4) *V1

R5, R6, and R7 are the shunt resistance. R8, R9, R10, C1, C2, and C3 are noise filters. Please connect it if necessary.

The above value is a theory value. Please set it after an enough evaluation.

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THERMAL DERATING



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